

AMENDMENTS TO THE CLAIMS

Claims 1 – 33 (canceled)

34. (original) A method of reading a resistive memory device comprising a plurality of stacked layers of resistive memory cells, each layer comprising an array of memory cells arranged in rows and columns, said method comprising:

accessing a selected memory cell by activating a row line coupled to a first side of said selected memory cell and turning on an access transistor which couples a second side of a plurality of memory cells in the same column of each said layer, to a sense amplifier.

35. (original) A method as in claim 34, wherein said resistive memory cells are MRAM memory cells.

36. (original) A method as in claim 34 further comprising sensing a resistance value of a selected memory cell with said sense amplifier.

Claims 37 – 61 (canceled)